

# NTP8N50, NTB8N50

Preferred Device

Advance Information

## Power MOSFET 8 Amps, 500 Volts N-Channel TO-220 and D2PAK

Designed for high voltage, high speed switching applications in power supplies, converters, power motor controls and bridge circuits.

### Features

- Higher Current Rating
- Lower  $R_{DS(on)}$
- Lower Capacitances
- Lower Total Gate Charge
- Tighter  $V_{SD}$  Specifications
- Avalanche Energy Specified

### Typical Applications

- Switch Mode Power Supplies
- PWM Motor Controls
- Converters
- Bridge Circuits

### MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	500	Vdc
Drain-Gate Voltage ( $R_{GS} = 1.0\text{ M}\Omega$ )	$V_{DGR}$	500	Vdc
Gate-Source Voltage			Vdc
– Continuous	$V_{GS}$	$\pm 20$	
– Non-Repetitive ( $t_p \leq 10\text{ ms}$ )	$V_{GSM}$	$\pm 40$	
Drain			Adc
– Continuous	$I_D$	8.0	
– Continuous @ $100^\circ\text{C}$	$I_D$	6.2	
– Single Pulse ( $t_p \leq 10\text{ }\mu\text{s}$ )	$I_{DM}$	28	
Total Power Dissipation Derate above $25^\circ\text{C}$	$P_D$	202 1.61	Watts $\text{W}/^\circ\text{C}$
Operating and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$
Single Drain-to-Source Avalanche Energy – Starting $T_J = 25^\circ\text{C}$ ( $V_{DD} = 100\text{ Vdc}$ , $V_{GS} = 10\text{ Vdc}$ , $I_L = 8\text{ A}$ , $L = 10\text{ mH}$ , $R_G = 25\text{ }\Omega$ )	$E_{AS}$	320	mJ
Thermal Resistance			$^\circ\text{C}/\text{W}$
– Junction-to-Case	$R_{\theta JC}$	0.62	
– Junction-to-Ambient	$R_{\theta JA}$	62.5	
– Junction-to-Ambient (Note 1.)	$R_{\theta JA}$	50	
Maximum Lead Temperature for Soldering Purposes, $1/8''$ from case for 10 seconds	$T_L$	260	$^\circ\text{C}$

1. When surface mounted to an FR4 board using the minimum recommended pad size.

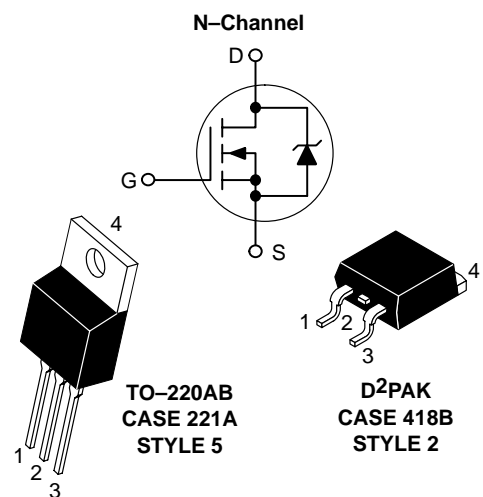
This document contains information on a new product. Specifications and information herein are subject to change without notice.



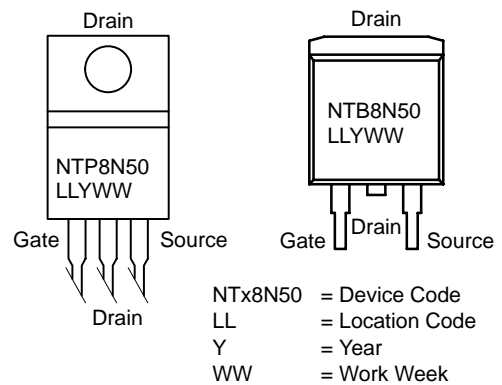
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**8 AMPERES**  
**500 VOLTS**  
 **$R_{DS(on)} = 750\text{ m}\Omega$**



### MARKING DIAGRAMS AND PIN ASSIGNMENTS



### ORDERING INFORMATION

Device	Package	Shipping
NTP8N50	TO-220AB	50 Units/Rail
NTB8N50	D2PAK	50 Units/Rail
NTB8N50T4	D2PAK	800/Tape & Reel

Preferred devices are recommended choices for future use and best overall value.

# NTP8N50, NTB8N50

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Drain-to-Source Breakdown Voltage (V <sub>GS</sub> = 0 Vdc, I <sub>D</sub> = 0.25 mAdc) Temperature Coefficient (Positive)	V <sub>(BR)DSS</sub>	500 –	– 560	– –	Vdc mV/°C
Zero Gate Voltage Collector Current (V <sub>DS</sub> = 500 Vdc, V <sub>GS</sub> = 0 Vdc) (V <sub>DS</sub> = 500 Vdc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 125°C)	I <sub>DSS</sub>	– –	– –	10 100	μAdc
Gate-Body Leakage Current (V <sub>GS</sub> = ±20 Vdc, V <sub>DS</sub> = 0)	I <sub>GSS(f)</sub> I <sub>GSS(r)</sub>	– –	– –	100 100	nAdc

## ON CHARACTERISTICS (Note 2.)

Gate Threshold Voltage I <sub>D</sub> = 0.25 mA, V <sub>DS</sub> = V <sub>GS</sub> Temperature Coefficient (Negative)	V <sub>GS(th)</sub>	2.0 –	2.6 6.5	4.0 –	Vdc mV/°C
Static Drain-to-Source On-Resistance (V <sub>GS</sub> = 10 Vdc, I <sub>D</sub> = 4.0 Adc)	R <sub>DS(on)</sub>	–	600	750	mOhm
Drain-to-Source On-Voltage (V <sub>GS</sub> = 10 Vdc, I <sub>D</sub> = 8.0 Adc) (V <sub>GS</sub> = 10 Vdc, I <sub>D</sub> = 4.0 Adc, T <sub>J</sub> = 125°C)	V <sub>DS(on)</sub>	– –	– –	7.2 6.3	Vdc
Forward Transconductance (V <sub>DS</sub> = 15 Vdc, I <sub>D</sub> = 4.0 Adc)	g <sub>FS</sub>	4.0	7.0	–	Mhos

## DYNAMIC CHARACTERISTICS

Input Capacitance	(V <sub>DS</sub> = 25 Vdc, V <sub>GS</sub> = 0 Vdc, f = 1.0 MHz)	C <sub>iss</sub>	–	1530	2140	pF
Output Capacitance		C <sub>oss</sub>	–	380	530	
Transfer Capacitance		C <sub>rss</sub>	–	15	30	

## SWITCHING CHARACTERISTICS (Note 3.)

Turn-On Delay Time	(V <sub>DD</sub> = 250 Vdc, I <sub>D</sub> = 12 Adc, V <sub>GS</sub> = 10 Vdc, R <sub>G</sub> = 9.1 Ω)	t <sub>d(on)</sub>	–	14	30	ns
Rise Time		t <sub>r</sub>	–	17	30	
Turn-Off Delay Time		t <sub>d(off)</sub>	–	34	70	
Fall Time		t <sub>f</sub>	–	25	50	
Gate Charge	(V <sub>DS</sub> = 400 Vdc, I <sub>D</sub> = 8.0 Adc, V <sub>GS</sub> = 10 Vdc)	Q <sub>T</sub>	–	25	40	nC
		Q <sub>1</sub>	–	6.0	–	
		Q <sub>2</sub>	–	8.0	–	
		Q <sub>3</sub>	–	12	–	

## SOURCE-DRAIN DIODE CHARACTERISTICS

Forward On-Voltage (Note 2.)	(I <sub>S</sub> = 8.0 Adc, V <sub>GS</sub> = 0 Vdc) (I <sub>S</sub> = 8.0 Adc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 125°C)	V <sub>SD</sub>	– –	0.9 0.8	1.1 –	Vdc
Reverse Recovery Time	(I <sub>S</sub> = 8.0 Adc, V <sub>GS</sub> = 0 Vdc, dI <sub>S</sub> /dt = 100 A/μs)	t <sub>rr</sub>	–	375	–	ns
		t <sub>a</sub>	–	155	–	
		t <sub>b</sub>	–	220	–	
Reverse Recovery Stored Charge		Q <sub>R</sub>	–	2.75	–	μC

## INTERNAL PACKAGE INDUCTANCE

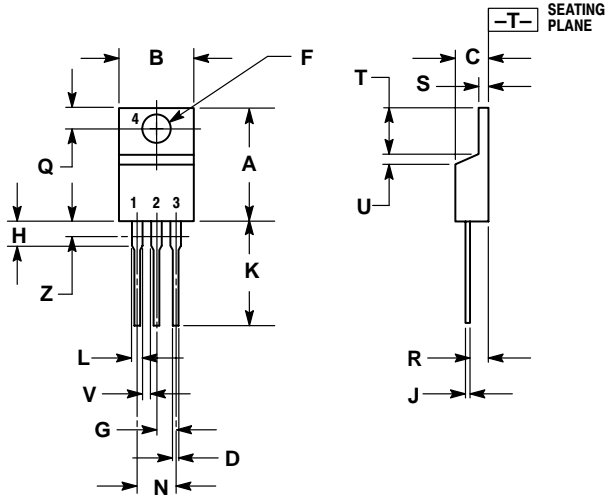
Internal Drain Inductance (Measured from contact screw on tab to center of die) (Measured from the drain lead 0.25" from package to center of die)	L <sub>D</sub>	– –	3.5 4.5	– –	nH
Internal Source Inductance (Measured from the source lead 0.25" from package to source bond pad)	L <sub>S</sub>	–	7.5	–	

- Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
- Switching characteristics are independent of operating junction temperature.

# NTP8N50, NTB8N50

## PACKAGE DIMENSIONS

TO-220 THREE-LEAD  
TO-220AB  
CASE 221A-09  
ISSUE AA



NOTES:

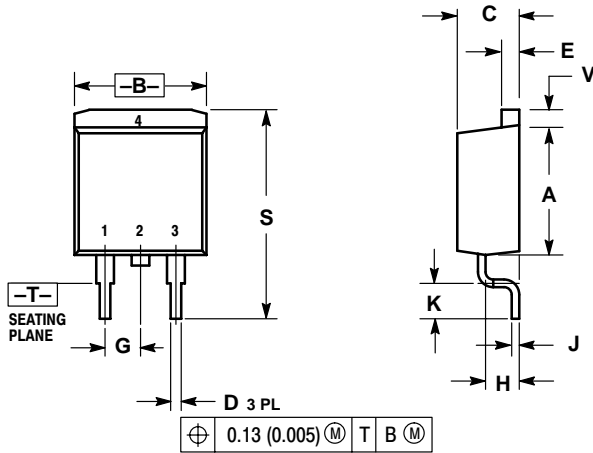
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 5:

- PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN

D<sup>2</sup>PAK  
CASE 418B-03  
ISSUE D



NOTES:


1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

STYLE 2:

- PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN

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